SN74LVC258A Quadruple 2-Line To 1-Line Inverting Data Selectors or Multiplexers With 3-State Outputs

1 Features

- Operating range from 1.1V to 3.6V
- Over-voltage tolerant inputs support up to 5.5V independent of V_{CC}
- Supports partial-power-down with back drive protection (I_{off})
- High push-pull output drive strength:
  - ±24mA at 3.3V
  - ±8mA at 2.3V
  - ±4mA at 1.65V
- Maximum propagation delay of 6.4ns at 3.3V supply
- Latch-up performance exceeds 100mA per JESD78

2 Applications

- Data selection
- Multiplexing

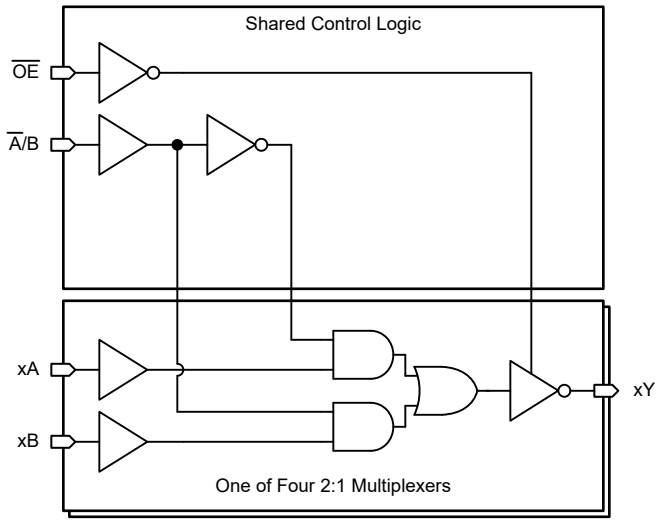
3 Description

The SN74LVC258A contains four 2-to-1 digital multiplexers with inverted outputs. The output enable ($\overline{OE}$) and select ($\overline{A}$/B) inputs control all channels.

Package Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)	BODY SIZE (NOM)(3)
SN74LVC258A	D (SOIC, 16)	9.9mm × 6mm	9.9mm × 3.9mm
	PW (TSSOP, 16)	5mm × 6.4mm	5mm × 4.4mm

(1) For more information, see Section 11.
(2) The package size (length × width) is a nominal value and includes pins, where applicable
(3) The body size (length × width) is a nominal value and does not include pins.



Functional Diagram

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4 Pin Configuration and Functions

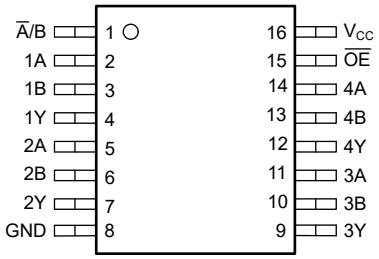


Figure 4-1. D or PW Package, 16-Pin SOIC or TSSOP (Top View)

Table 4-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.		
$\overline{A}$/B	1	I	Select data source
1A	2	I	Channel 1, input A
1B	3	I	Channel 1, input B
1Y	4	O	Channel 1, output Y
2A	5	I	Channel 2, input A
2B	6	I	Channel 2, input B
2Y	7	O	Channel 2, output Y
GND	8	G	Ground
3Y	9	O	Channel 3, output Y
3B	10	I	Channel 3, input B
3A	11	I	Channel 3, input A
4Y	12	O	Channel 4, output Y
4B	13	I	Channel 4, input B
4A	14	I	Channel 4, input A
$\overline{OE}$	15	I	Output enable, active low
V_{CC}	16	P	Positive Supply

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	6.5	V
V_I	Input voltage range(2)		-0.5	6.5	V
V_O	Output voltage range(2)	High or low state	-0.5	V_{CC} + 0.5	V
		High-impedance state	-0.5	6.5	V
I_{IK}	Input clamp current	V_I < 0V		-50	mA
I_{OK}	Output clamp current	V_O < 0V		-50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		-65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The input and output negative voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002(2)	±1000	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		1.1	3.6	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
V_O	Output voltage	High-impedance state	0	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 1.1V	0.75		V
		V_{CC} = 1.2V	0.78		V
		V_{CC} = 1.5V	0.975		V
		V_{CC} = 1.65V	1.0725		V
		V_{CC} = 1.95V	1.2675		V
		V_{CC} = 2.3V	1.7		V
		V_{CC} = 2.7V	1.7		V
		V_{CC} = 3.6V	2		V

5.3 Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{IL}	Low-Level input voltage	V_{CC} = 1.1V		0.40	V
		V_{CC} = 1.2V		0.42	V
		V_{CC} = 1.5V		0.525	V
		V_{CC} = 1.65V		0.5775	V
		V_{CC} = 1.95V		0.6825	V
		V_{CC} = 2.3V		0.7	V
		V_{CC} = 2.7V		0.7	V
		V_{CC} = 3.6V		0.8	V
I_{OH}	High-level output current	V_{CC} = 1.8V		-4	mA
		V_{CC} = 2.3V		-8	
		V_{CC} = 2.7V		-12	
		V_{CC} = 3V		-24	
I_{OL}	Low-level output current	V_{CC} = 1.8V		4	mA
		V_{CC} = 2.3V		8	
		V_{CC} = 2.7V		12	
		V_{CC} = 3V		24	
Δt/Δv	Input transition rise or fall rate			10	ns/V
T_A	Operating free-air temperature		-40	125	°C

5.4 Thermal Information

PACKAGE	PINS	THERMAL METRIC(1)						UNIT
		$R_{\theta JA}$	$R_{\theta JC(top)}$	$R_{\theta JB}$	Ψ_{JT}	Ψ_{JB}	$R_{\theta JC(bot)}$	
D (SOIC)	16	109.1	70.8	67.3	34.1	67.1	-	°C/W
PW (TSSOP)	16	141.8	74	87.1	22.3	86.6	-	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	-40°C to 125°C			UNIT
			MIN	TYP	MAX	
V_{OH}	I_{OH}= –100µA	1.1V to 3.6V	V_{CC} - 0.2	V_{CC} - 0.01		V
V_{OH}	I_{OH}= –4mA	1.65V	1.2			V
V_{OH}	I_{OH}= –8mA	2.3V	1.75			V
V_{OH}	I_{OH}= –12mA	2.7V	2.2			V
V_{OH}		3V	2.4			V
V_{OH}	I_{OH}= –24mA	3V	2.2			V
V_{OL}	I_{OL} = 100µA	1.1V to 3.6V		0.01	0.2	V
V_{OL}	I_{OL} = 4mA	1.65V			0.45	V
V_{OL}	I_{OL} = 8mA	2.3V			0.7	V
V_{OL}	I_{OL} = 12mA	2.7V		0.2	0.4	V
V_{OL}	I_{OL} = 24mA	3V			0.55	V
I_I	V_I = V_{CC} or GND	3.6V			±5	µA

5.5 Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	-40°C to 125°C			UNIT
			MIN	TYP	MAX	
I_{off}	V_I or V_O = V_{CC}	0V			±10	µA
I_{OZ}	V_O = V_{CC} or GND	3.6V			±15	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6V			40	µA
ΔI_{CC}	One input at V_{CC} - 0.6V, other inputs at V_{CC} or GND	2.7V to 3.6V			5000	µA
C_I	V_I = V_{CC} or GND	3.3V		4.9		pF
C_O	V_O = V_{CC} or GND	3.3V		6.3		pF
C_{PD}	f = 10MHz	1.8V		12		pF
C_{PD}	f = 10MHz	2.5V		15		pF
C_{PD}	f = 10MHz	3.3V		17		pF
C_{PD}	Outputs disabled, f = 10MHz	1.8V		2		pF
		2.5V		3		
		3.3V		4		

5.6 Switching Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V_{CC}	T_A = 25°C			-40°C to 85°C			-40°C to 125°C			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{pd}	A or B	Y	C_L = 15pF	1.2V ± 0.1V		16						13.7	25	ns
			C_L = 15pF	1.5V ± 0.12V		14						7.7	13.3	ns
			C_L = 30pF	1.8V ± 0.15V		5.5	13.5	1		13.5		5.5	15.5	ns
			C_L = 30pF	2.5V ± 0.2V		3.2	7.4	1		7.4		3.7	10	ns
			C_L = 50pF	2.7V		3.6	5.7	1		5.4		3.7	7.4	ns
			C_L = 50pF	3.3V ± 0.3V		3	5	1		4.6		3.4	6.4	ns
	$\overline{A}$/B	Y	C_L = 15pF	1.2V ± 0.1V		17						15	26.2	ns
			C_L = 15pF	1.5V ± 0.12V		16						8.5	14	ns
			C_L = 30pF	1.8V ± 0.15V		6	15.5	1		15.6		6.3	17.5	ns
			C_L = 30pF	2.5V ± 0.2V		3.7	9.6	1		9.5		4.4	12.2	ns
			C_L = 50pF	2.7V		4.1	7.9	1		7.5		4.4	10	ns
			C_L = 50pF	3.3V ± 0.3V		3.4	6.6	1		6.4		4.1	8.4	ns

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V_{CC}	T_A = 25°C			-40°C to 85°C			-40°C to 125°C			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{en}	$\overline{OE}$	Y	C_L = 15pF	1.2V ± 0.1V		16						13.1	20.6	ns
			C_L = 15pF	1.5V ± 0.12V		15						7.2	10.6	ns
			C_L = 30pF	1.8V ± 0.15V				1		14.6		7.3	8.6	ns
			C_L = 30pF	2.5V ± 0.2V				1		8.7		4.8	5.7	ns
			C_L = 50pF	2.7V				1		6.7		5.2	6.7	ns
			C_L = 50pF	3.3V ± 0.3V				1		5.6		4.4	5.4	ns
t_{dis}	$\overline{OE}$	Y	C_L = 15pF	1.2V ± 0.1V		17						12	17	ns
			C_L = 15pF	1.5V ± 0.12V		16						7.5	10.3	ns
			C_L = 30pF	1.8V ± 0.15V				1		15.4		7.9	15.4	ns
			C_L = 30pF	2.5V ± 0.2V				1		6.7		4.7	6.7	ns
			C_L = 50pF	2.7V			4.8	1		5.2		4.9	5.5	ns
			C_L = 50pF	3.3V ± 0.3V			4.4	1		4.9		4.6	5.1	ns
$t_{sk(o)}$				3.3V ± 0.3V						1			1.5	ns

5.7 Noise Characteristics

VCC = 3.3V, CL = 50pF, TA = 25°C

PARAMETER	DESCRIPTION	MIN	TYP	MAX	UNIT
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}			0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}	-0.8	-0.3		V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}	2.2	3.3		V
$V_{IH(D)}$	High-level dynamic input voltage	2.0			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.8	V

5.8 Typical Characteristics

T_A = 25°C (unless otherwise noted)

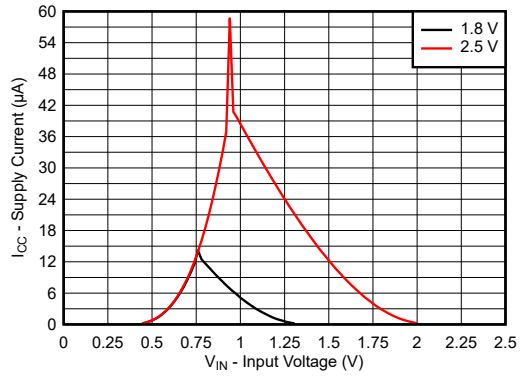


Figure 5-1. Supply Current Across Input Voltage 1.8V and 2.5V Supply

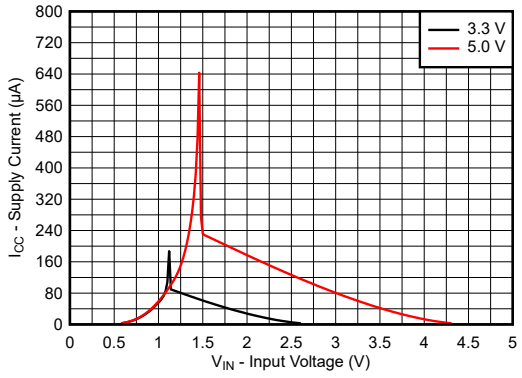


Figure 5-2. Supply Current Across Input Voltage 3.3V and 5.0V Supply

5.8 Typical Characteristics (continued)

T_A = 25°C (unless otherwise noted)

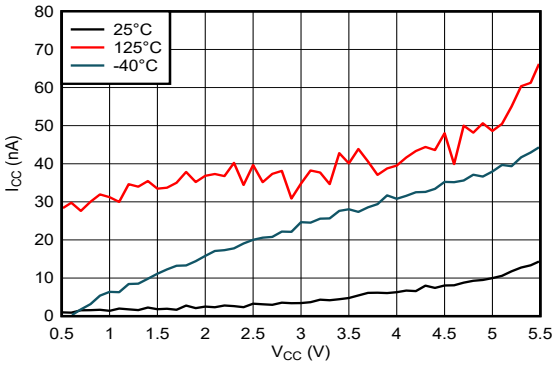


Figure 5-3. Supply Current Across Supply Voltage

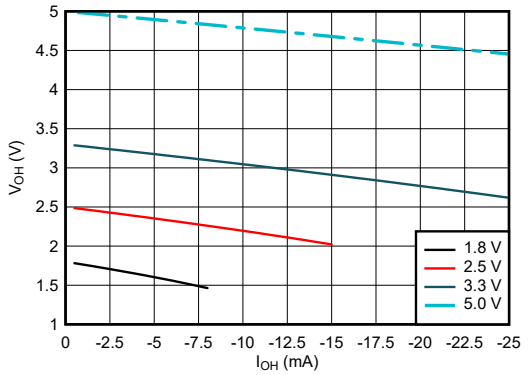


Figure 5-4. Output Voltage vs Current in HIGH State

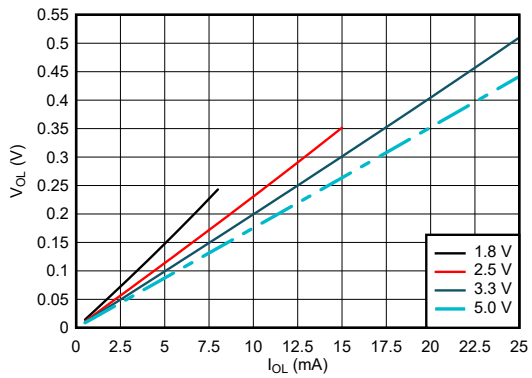


Figure 5-5. Output Voltage vs Current in LOW State

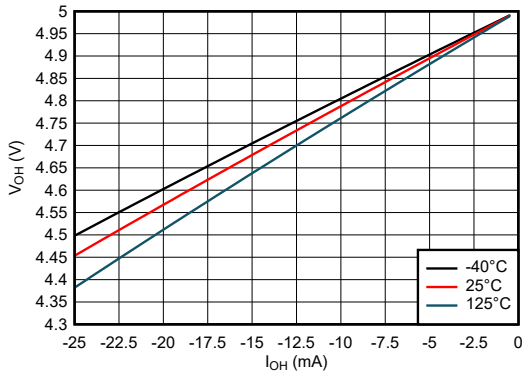


Figure 5-6. Output Voltage vs Current in HIGH State; 5V Supply

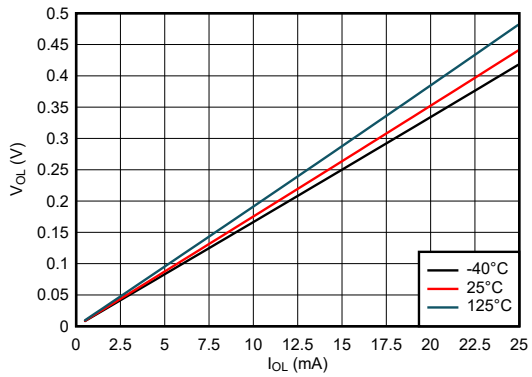


Figure 5-7. Output Voltage vs Current in LOW State; 5V Supply

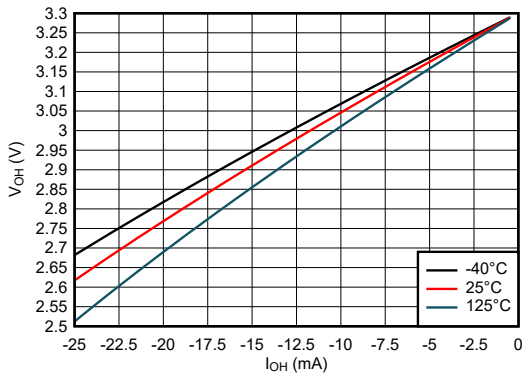


Figure 5-8. Output Voltage vs Current in HIGH State; 3.3V Supply

5.8 Typical Characteristics (continued)

T_A = 25°C (unless otherwise noted)

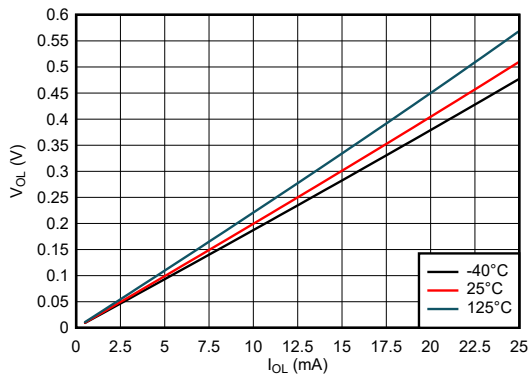


Figure 5-9. Output Voltage vs Current in LOW State; 3.3V Supply

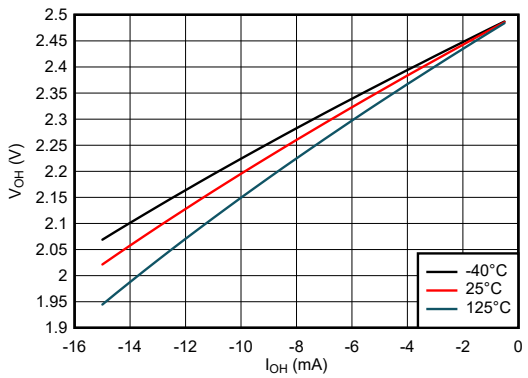


Figure 5-10. Output Voltage vs Current in HIGH State; 2.5V Supply

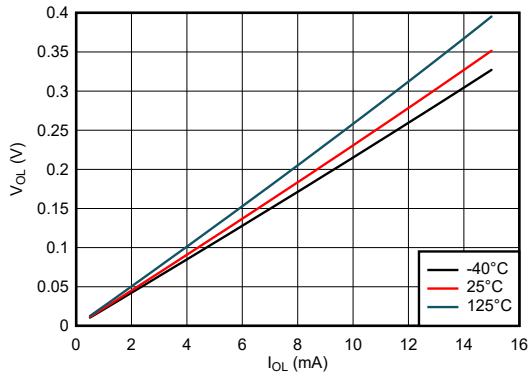


Figure 5-11. Output Voltage vs Current in LOW State; 2.5V Supply

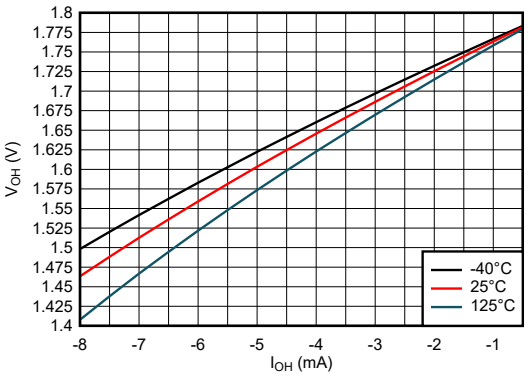


Figure 5-12. Output Voltage vs Current in HIGH State; 1.8V Supply

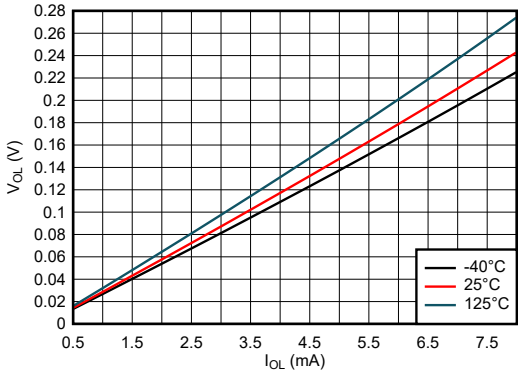


Figure 5-13. Output Voltage vs Current in LOW State; 1.8V Supply

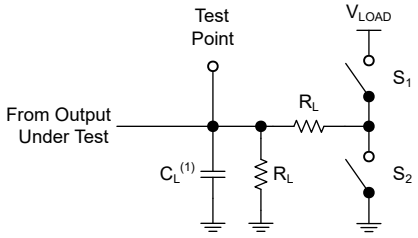
6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1MHz, Z_O = 50Ω, t_t ≤ 2.5ns.

The outputs are measured individually with one input transition per measurement.

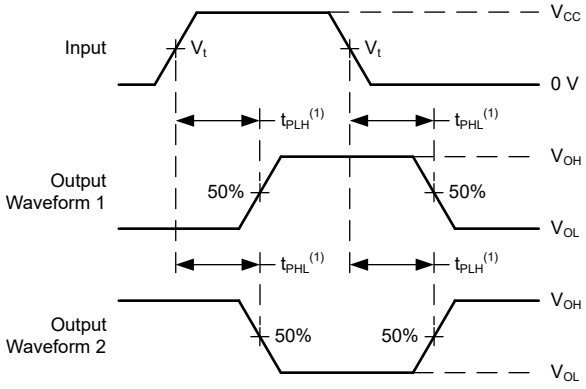
TEST	S1	S2	R_L	C_L	ΔV	V_{LOAD}
t_{PLH}, t_{PHL}	OPEN	OPEN	500Ω	50pF	—	—
t_{PLZ}, t_{PZL}	CLOSED	OPEN	500Ω	50pF	0.3V	2×V_{CC}
t_{PHZ}, t_{PZH}	OPEN	CLOSED	500Ω	50pF	0.3V	—

V_{CC}	V_t	R_L	C_L	ΔV	V_{LOAD}
1.2V ± 0.1V	V_{CC}/2	2kΩ	15pF	0.1V	2×V_{CC}
1.5V ± 0.12V	V_{CC}/2	2kΩ	15pF	0.1V	2×V_{CC}
1.8V ± 0.15V	V_{CC}/2	1kΩ	30pF	0.15V	2×V_{CC}
2.5V ± 0.2V	V_{CC}/2	500Ω	30pF	0.15V	2×V_{CC}
2.7V	1.5V	500Ω	50pF	0.3V	6V
3.3V ± 0.3V	1.5V	500Ω	50pF	0.3V	6V



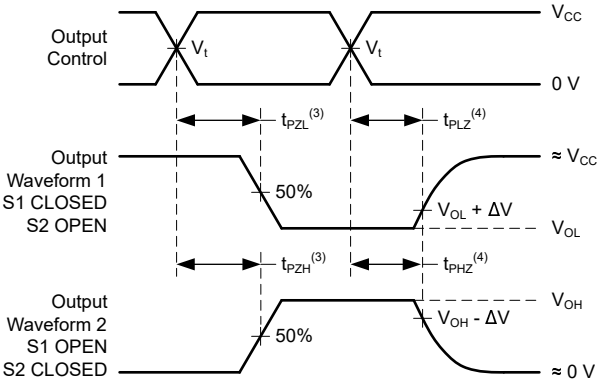
(1) C_L includes probe and test-fixture capacitance.

Figure 6-1. Load Circuit for 3-State Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

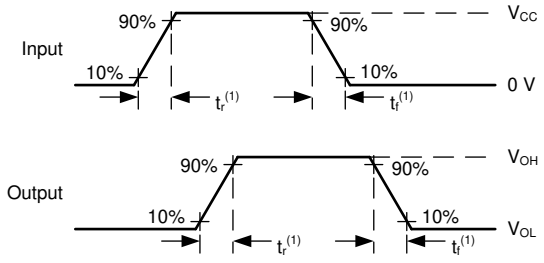
Figure 6-2. Voltage Waveforms Propagation Delays



(1) The greater between t_{PZL} and t_{PZH} is the same as t_{en}.

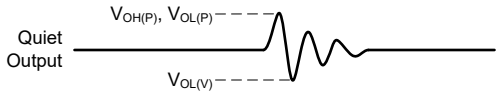
(2) The greater between t_{PLZ} and t_{PHZ} is the same as t_{dis}.

Figure 6-3. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t.

Figure 6-4. Voltage Waveforms, Input and Output Transition Times



Noise values measured with all other outputs simultaneously switching.

Figure 6-5. Voltage Waveforms, Noise

7 Detailed Description

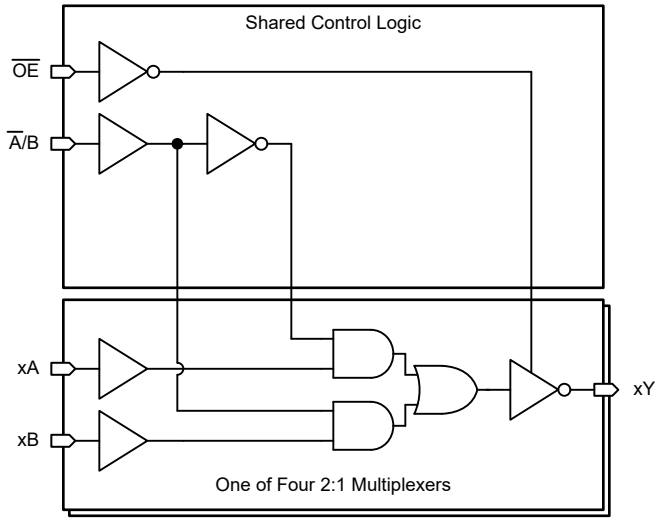
7.1 Overview

The SN74LVC258A is a 4 channel 2-to-1 multiplexer with inverted outputs.

The output enable ($\overline{OE}$) input enables all outputs when low, and forces all outputs into the high-impedance state when high.

The select ($\overline{A}$/B) input chooses the data source for all channels, with the low state indicating the A data source, and the high state indicating the B data source.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance state, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10kΩ resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

7.3.2 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

7.3.3 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a 10kΩ resistor, however, is recommended and will typically meet all requirements.

7.3.4 Clamp Diode Structure

Figure 7-1 shows the inputs and outputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

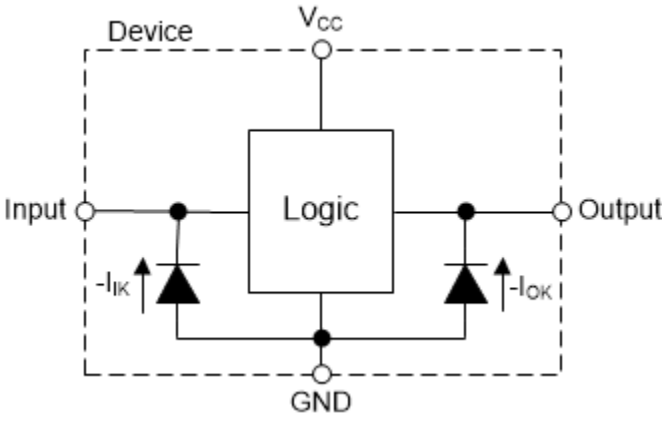


Figure 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Function Table lists the functional modes of the SN74LVC258A.

Table 7-1. Function Table

INPUTS(1)				OUTPUT(2)
$\overline{OE}$	SELECT	DATA		
	$\overline{A}$/B	A	B	Y
H	X	X	X	Z
L	L	L	X	H
L	L	H	X	L
L	H	X	L	H
L	H	X	H	L

(1) H = High voltage level, L = Low voltage level, X = Don't care

(2) H = Driving high, L = Driving low

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74LVC258A is a quadruple 2-to-1 data selector/multiplexer with inverted outputs. The following application shows an example of using the device with all required connections to switch a 4-bit data bus between two source devices.

8.2 Typical Application

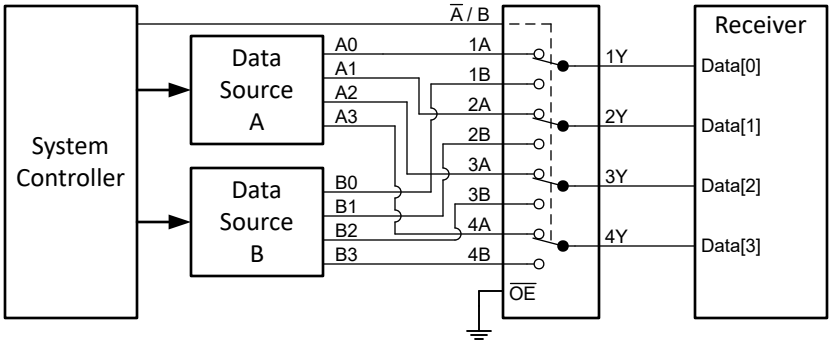


Figure 8-1. Typical Application Block Diagram

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LVC258A plus the maximum static supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Ensure the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LVC258A plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74LVC258A can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN74LVC258A can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL}. When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices*.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LVC258A (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10kΩ resistor value is often used due to these factors.

The SN74LVC258A has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74LVC258A to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than (V_{CC} / $I_{O(max)}$)Ω. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in MΩ; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

8.2.3 Application Curve

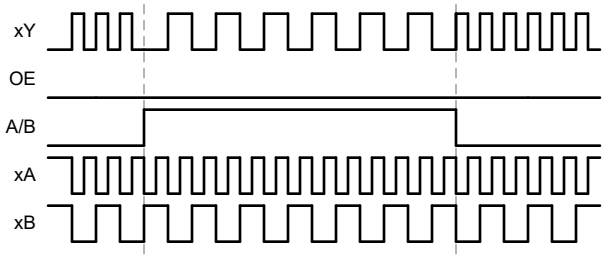


Figure 8-2. Application Timing Diagram

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions*.

During startup, the power supply should ramp within the provided power-up ramp rate range in the *Recommended Operating Conditions* table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For the SN74LVC258A, a 0.1µF bypass capacitor is recommended. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1µF and 1µF are commonly used in parallel.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

8.4.2 Layout Example

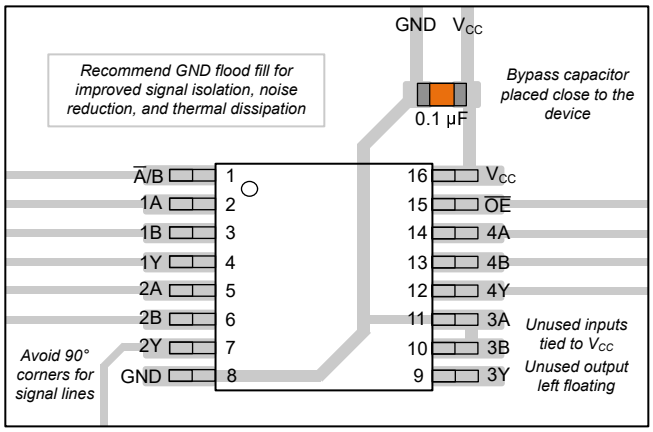


Figure 8-3. Example Layout for the SN74LVC258A

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *CMOS Power Consumption and Cpd Calculation* application note
- Texas Instruments, *Designing With Logic* application note
- Texas Instruments, *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices* application note
- Texas Instruments, *Implications of Slow or Floating CMOS Inputs* application note

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
July 2024	*	Initial Release

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74LVC258ADR	Active	Production	SOIC (D) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC258A
SN74LVC258ADR.A	Active	Production	SOIC (D) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC258A
SN74LVC258APWR	Active	Production	TSSOP (PW) | 16	3000 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	LVC258
SN74LVC258APWR.A	Active	Production	TSSOP (PW) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC258

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

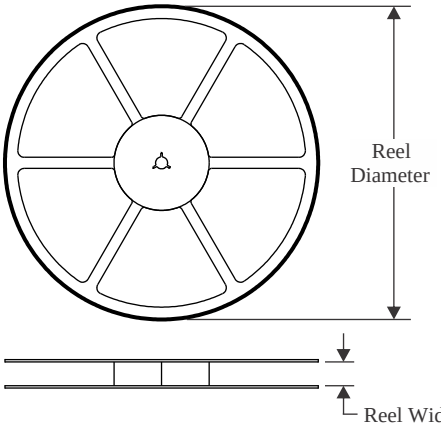
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

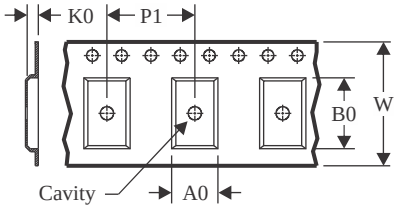
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

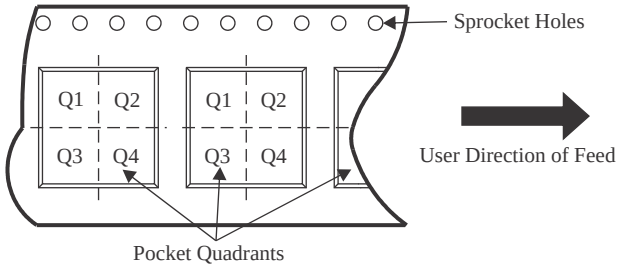


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

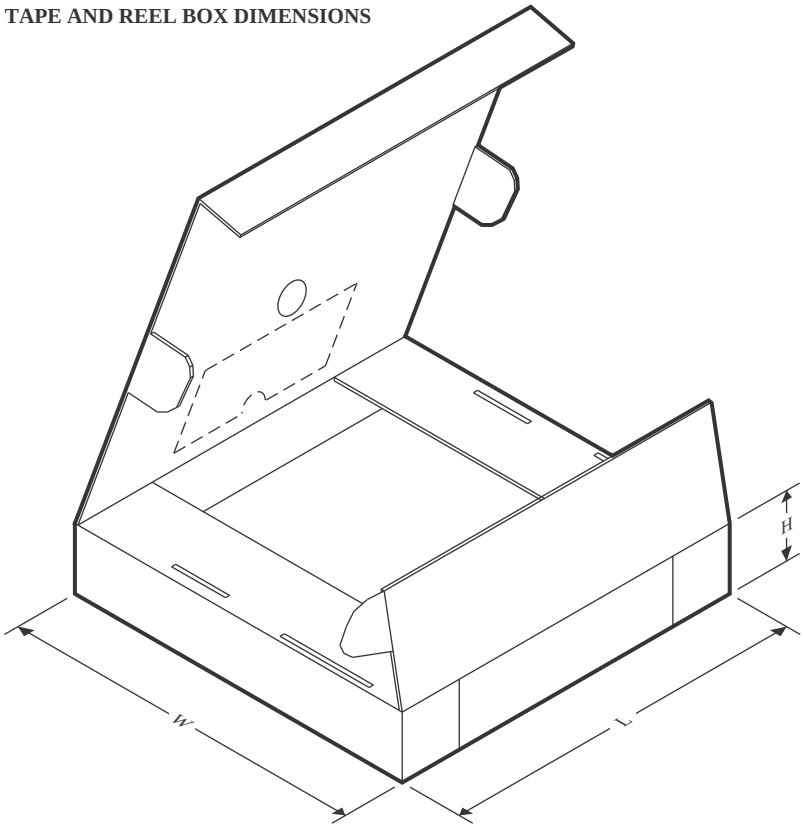
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC258ADR	SOIC	D	16	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1
SN74LVC258ADR	SOIC	D	16	3000	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74LVC258APWR	TSSOP	PW	16	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

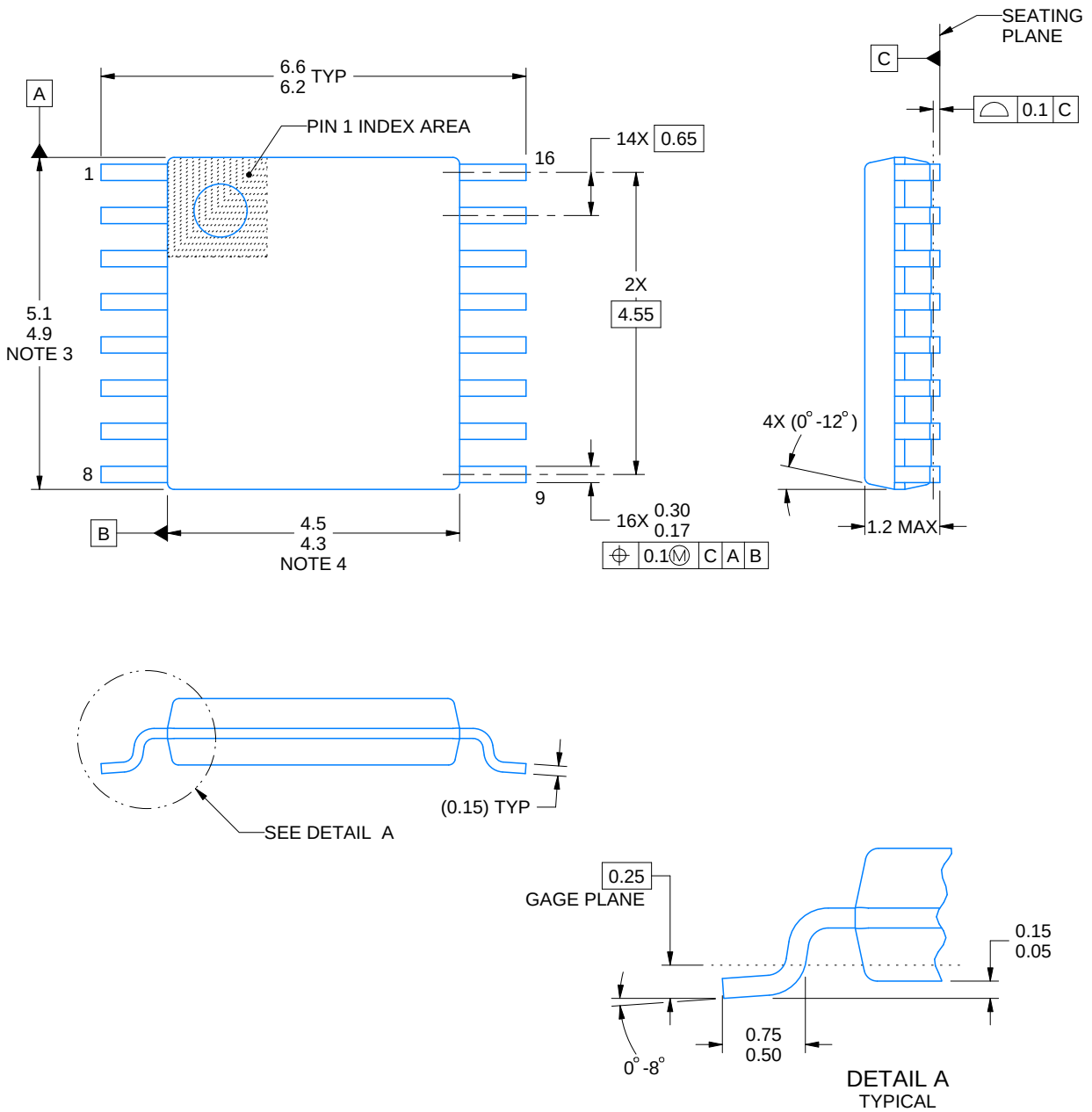
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC258ADR	SOIC	D	16	3000	340.5	336.1	32.0
SN74LVC258ADR	SOIC	D	16	3000	353.0	353.0	32.0
SN74LVC258APWR	TSSOP	PW	16	3000	353.0	353.0	32.0

PACKAGE OUTLINE

PW0016A

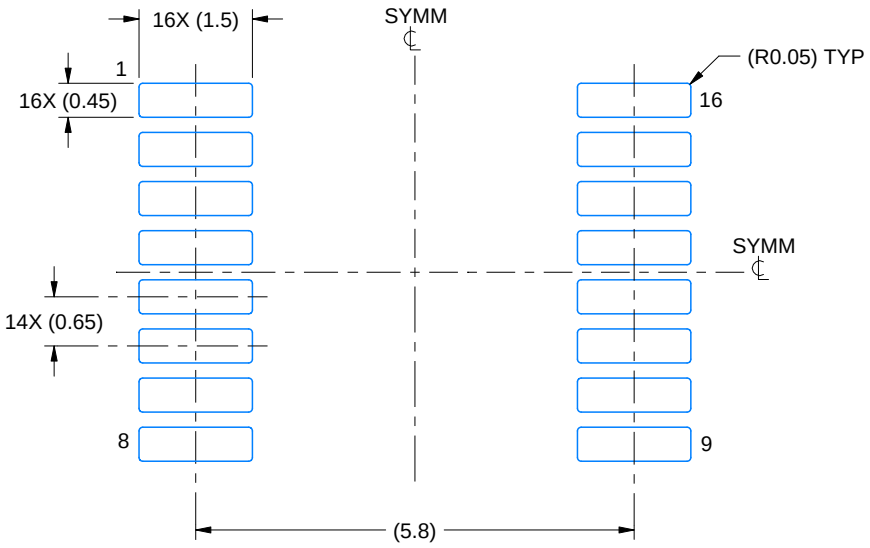
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



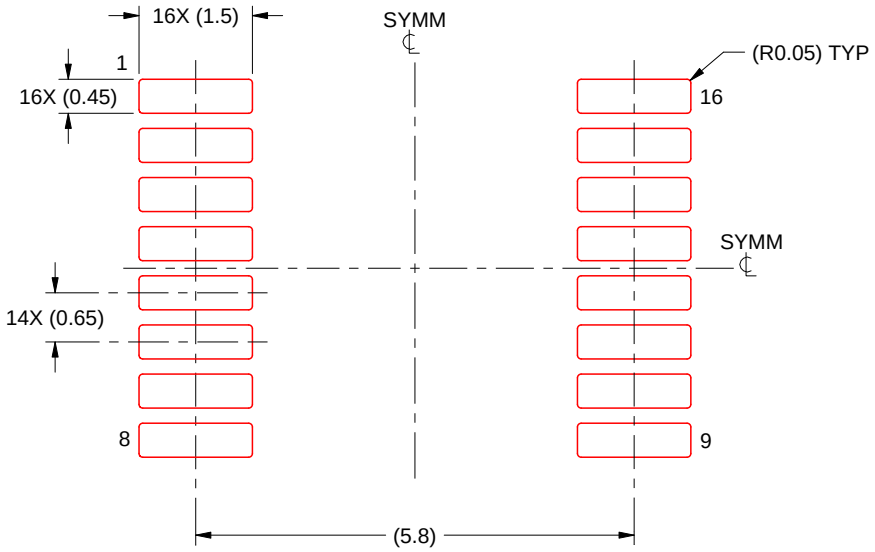
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

4220204/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



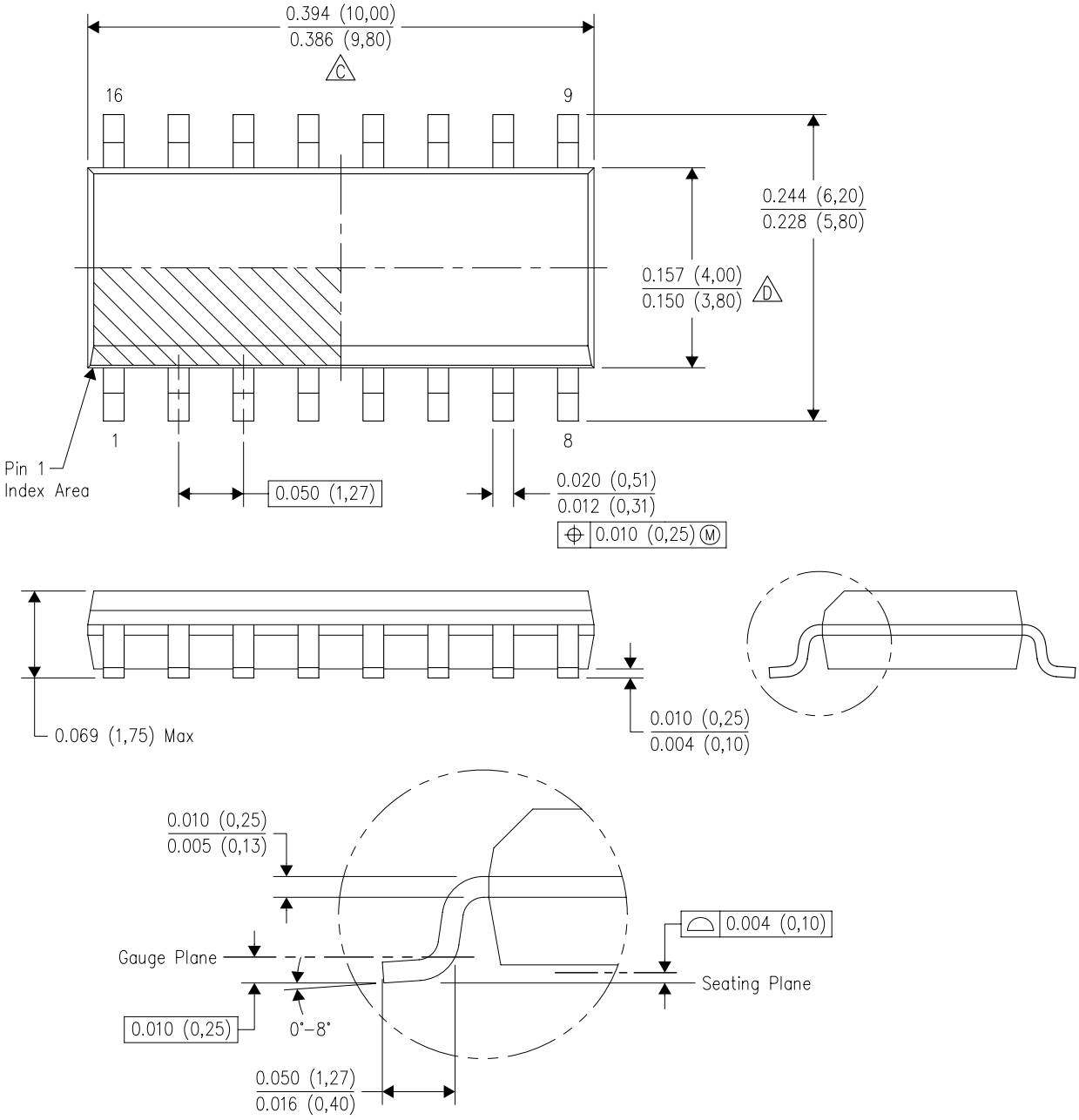
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

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